L Number	Hits	Search Text	DB	Time stamp
7	104	organic adj2 switch\$3	USPAT; US-PGPUB;	2004/09/15 13:55
9	17	(organic adj2 switch\$3) and (first adj3 electrode)	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 13:56
10	15	((organic adj2 switch\$3) and (first adj3 electrode)) and (second adj3 electrode)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 14:14
11	219	(first adj3 electrode) same organic same diod\$2	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 13:59
12	10	((first adj3 electrode) same organic same diod\$2) same (second adj3 electrode) same memory	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 13:59
8	7	(organic adj2 switch\$3) same (first adj3 electrode)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 14:17
14	2	("6055180").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/09/15 14:17
13	73	"6055180"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15
15	23	tanabe-takahisa.in.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15
16	0	tanabe-takahisa-\$.in.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 14:23
-	10	organic adj3 switch\$3 adj3 memory	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/09/15
	115	organic same (switch\$3 adj2 memory)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/09/15 11:56
-	5	(organic same (switch\$3 adj2 memory)) same (first adj2 electrode)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/15 11:57

-	16	(first adj2 electrod\$2) same (organic	USPAT;	2004/09/15
		adj3 memory)	US-PGPUB;	12:01
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	11	(organic same (switch\$3 adj2 memory)) and	USPAT;	2004/09/15
		((first adj2 electrod\$2) same (organic	US-PGPUB;	12:01
		adj3 memory))	EPO; JPO;	12.01
	1	adjo memory//	DERWENT;	
	20	/6:t	IBM_TDB USPAT;	2004/00/15
-	39			2004/09/15
		memory) and (second electrod\$2)	US-PGPUB;	12:01
			EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	
-	22		USPAT;	2004/09/15
		adj3 memory) and (second electrod\$2)) and	US-PGPUB;	12:02
		diode	EPO; JPO;	
			DERWENT;	
	ľ		IBM TDB	
_	11	(((first adj2 electrod\$2) and (organic	USPAT;	2004/09/15
		adj3 memory) and (second electrod\$2)) and	US-PGPUB;	12:07
	I	diode) and (organic same (switch\$3 adj2	EPO; JPO;	-2.07
	1	memory))	DERWENT;	
	1	memory)		
	1	/44646 6440 160500	IBM_TDB	2004/00/15
-	19	1, , , , , , , , , , , , , , , , , , ,	USPAT;	2004/09/15
		electrode)	US-PGPUB;	12:07
		·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	15	((diode adj2 layer) near5 (second adj2	USPAT;	2004/09/15
		electrode)) near5 (first adj2 electrode)	US-PGPUB;	12:07
			EPO; JPO;	
			DERWENT;	
1			IBM TDB	
_	7	((((diode adj2 layer) near5 (second adj2	USPAT;	2004/09/15
	,	electrode)) near5 (first adj2 electrode))	US-PGPUB;	12:10
		near10 organic) and (memory or	EPO; JPO;	12.10
	-	semiconductor)	DERWENT;	
		Semiconductor)		
	1 14		IBM_TDB	2004 (00 (15
-	14	(((diode adj2 layer) near5 (second adj2	USPAT;	2004/09/15
		electrode)) near5 (first adj2 electrode))	US-PGPUB;	12:09
		near10 organic	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	(low adj2 electrode) same (up adj2	USPAT;	2004/09/15
		electrode) same diode same resistor	US-PGPUB;	12:11
			EPO; JPO;	l i
	1		DERWENT;	
			IBM TDB	ļ
-	l 0	(low adj2 electrode) same (up adj2	USPAT;	2004/09/15
		electrode) same diode	US-PGPUB;	12:12
			EPO; JPO;	·
1			DERWENT;	
1			IBM TDB	
 _	3784	((low or lower or first) adj2 electrode)	USPAT;	2004/09/15
-	3/04			1
		same ((up or upper or high or second)	US-PGPUB;	12:13
		adj2 electrode) same diode	EPO; JPO;	
			DERWENT;	
]		(1/1)	IBM_TDB	0004/05/55
-	141	(((low or lower or first) adj2 electrode)	USPAT;	2004/09/15
		same ((up or upper or high or second)	US-PGPUB;	12:17
		adj2 electrode) same diode) same memory	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	5	((((low or lower or first) adj2	USPAT;	2004/09/15
[electrode) same ((up or upper or high or	US-PGPUB;	12:16
		second) adj2 electrode) same diode) same	EPO; JPO;	
		memory) same (organic adj2 memory)	DERWENT;	
	i	-1, (-rading and momory)	IBM TDB	
	1		~ D I D D	1

-	4	((((low or lower or first) adj2	USPAT;	2004/09/15
		electrode) same ((up or upper or high or	US-PGPUB;	12:17
		second) adj2 electrode) same diode) same	EPO; JPO;	
Ì		memory) same (organic adj2 layer)	DERWENT;	
		_	IBM TDB	
-	36	((((low or lower or first) adj2	USPAT;	2004/09/15
		electrode) same ((up or upper or high or	US-PGPUB;	13:53
		second) adj2 electrode) same diode) same	EPO; JPO;	
		memory) and 365/\$7.ccls.	DERWENT;	
			IBM_TDB	